

isc Silicon PNP Power Transistors
D45C6
DESCRIPTION

- Low Saturation Voltage
- Good Linearity of h_{FE}
- Fast Switching Speeds
- Complement to Type D44C6
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

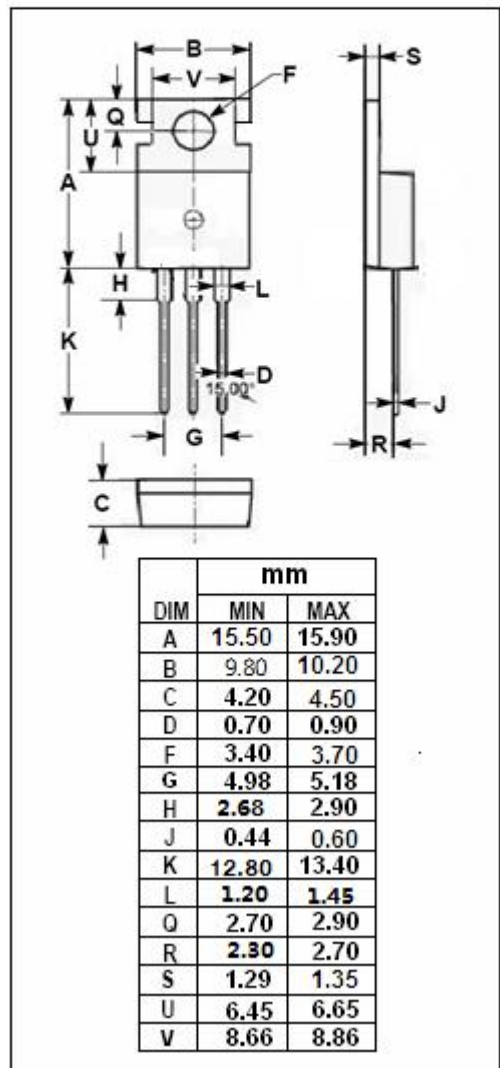
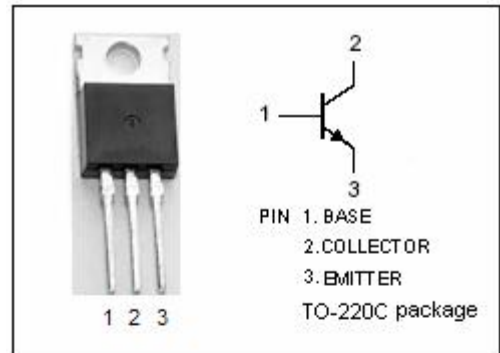
- Designed for various specific and general purpose application such as: output and driver stages of amplifiers operating at frequencies from DC to greater than 1.0MHz series, shunt and switching regulators; low and high frequency inverters/converters and many others.

ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

| SYMBOL | PARAMETER | VALUE | UNIT |
|-----------|---|---------|------------------|
| V_{CES} | Collector-Emitter Voltage | -55 | V |
| V_{CEO} | Collector-Emitter Voltage | -45 | V |
| V_{EBO} | Emitter-Base Voltage | -5 | V |
| I_C | Collector Current-Continuous | -4 | A |
| I_{CM} | Collector Current-Peak | -6 | A |
| I_B | Base Current-Continuous | -1 | A |
| P_C | Collector Power Dissipation @ $T_C=25^\circ\text{C}$ | 30 | W |
| T_j | Junction Temperature | 150 | $^\circ\text{C}$ |
| T_{stg} | Storage Temperature Range | -55~150 | $^\circ\text{C}$ |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | MAX | UNIT |
|---------------|--------------------------------------|-----|--------------------|
| $R_{th\ j-c}$ | Thermal Resistance, Junction to Case | 4.2 | $^\circ\text{C/W}$ |



ELECTRICAL CHARACTERISTICST_c=25°C unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP | MAX | UNIT |
|----------------------|--------------------------------------|---|-----|-----|------|------|
| V _{CE(sat)} | Collector-Emitter Saturation Voltage | I _C = -1A; I _B = -50mA | | | -0.5 | V |
| V _{BE(sat)} | Base-Emitter Saturation Voltage | I _C = -1A; I _B = -100mA | | | -1.3 | V |
| I _{CES} | Collector Cutoff Current | V _{CE} = -55V, V _{BE} = 0 | | | -10 | μ A |
| I _{EBO} | Emitter Cutoff Current | V _{EB} = -5V; I _C = 0 | | | -100 | μ A |
| h _{FE-1} | DC Current Gain | I _C = -0.2A; V _{CE} = -1V | 40 | | 120 | |
| h _{FE-2} | DC Current Gain | I _C = -2A; V _{CE} = -1V | 20 | | | |
| f _T | Current-Gain—Bandwidth Product | I _C = -20mA; V _{CE} = -4V; f _{test} = 1MHz | | 40 | | MHz |

Switching Times

| | | | | | | |
|----------------|--------------|---|--|--|-----|-----|
| t _r | Rise Time | I _C = -1A; I _{B1} = -I _{B2} = -0.1A; V _{CC} = -20V | | | 0.2 | μ s |
| t _s | Storage Time | | | | 0.6 | μ s |
| t _f | Fall Time | | | | 0.3 | μ s |

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